

1	<b>MAGNETIC BUBBLES</b>	185.08	..With volatile signal storage device
2	.Disposition of elements		
3	..Lattice	185.09	..Error correction (e.g., redundancy, endurance)
4	.Decoder		
5	.Logic	185.1	..Extended floating gate
6	.Rotating field circuits	185.11	..Bank or block architecture
7	.Detectors	185.12	...Parallel row lines (e.g., page mode)
8	..Magnetoresistive		
9	..Hall effect	185.13	...Global word or bit lines
10	..Optical	185.14	..Program gate
11	.Generators	185.15	...Weak inversion injection
12	..By splitting	185.16	..Virtual ground
13	.Plural interacting paths	185.17	..Logic connection (e.g., NAND string)
14	..Closed loop		
15	...Major-minor	185.18	.Particular biasing
16	..With switch at interacting point	185.19	..Multiple pulses (e.g., ramp)
17	...Idler switch	185.2	..Reference signal (e.g., dummy cell)
18	..Boundary	185.21	...Sensing circuitry (e.g., current mirror)
19	.Conductor propagation		
20	..Including A.C. signal	185.22	...Verify signal
21	..Three phase signals	185.23	..Drive circuitry (e.g., word line driver)
22	.One's and zero's		
23	.Plural direction propagation	185.24	..Threshold setting (e.g., conditioning)
24	..Nonsequential		
25	.Velocity	185.25	..Line charging (e.g., precharge, discharge, refresh)
26	..Turns		
27	.Bias	185.26	..Floating electrode (e.g., source, control gate, drain)
28	..Variable		
29	.Strip domain	185.27	..Substrate bias
30	.In-plane field (nonrotating)	185.28	..Tunnel programming
31	.Different size bubbles	185.29	..Erase
32	.Multiple magnetic layer	185.3	...Over erasure
33	.Magnetic storage material	185.31	...Nonsubstrate discharge
34	..Amorphous	185.32	...Radiation erasure
35	.Guide structure	185.33	...Flash
36	..Ion implantation	45	<b>ANALOG STORAGE SYSTEMS</b>
37	..Slots or rails	46	.Resistive
38	..Zigzag	47	.Thermoplastic
39	..Overlays	48	.Magnetic
40	...On opposite sides of storage medium	49	<b>ASSOCIATIVE MEMORIES</b>
41	...Dots	50	.Magnetic
42	...Wedges	51	<b>FORMAT OR DISPOSITION OF ELEMENTS</b>
43	...Chevrons	52	<b>HARDWARE FOR STORAGE ELEMENTS</b>
44	..Rectangular bars	53	.Shields
185.01	<b>FLOATING GATE</b>	54	.Ground plane
185.02	.Disturbance control	55	.Magnetic
185.03	.Multiple values (e.g., analog)	56	..Spacers
185.04	.Data security	57	..Keeper
185.05	.Particular connection	58	..Slot
185.06	..Segregated columns	59	..Embedded conductor
185.07	..Cross-coupled cell	60	..Air gap
		61	..Hairpin conductor

62	..Permanent magnet	111	.Electroluminescent
63	<b>INTERCONNECTION ARRANGEMENTS</b>	112	.Photoconductive
64	.Optical	113	.Amorphous
65	.Ferroelectric	114	.Semiconductive
66	.Magnetic	115	..Diodes
67	..Plural diagonal	116	.Plasma
68	..Tree	117	.Ferroelectric
69	..Crossover	118	.Electron beam
70	..Woven	119	.Color centers
71	.Negative resistance	120	<b>INFORMATION MASKING</b>
72	.Transistors or diodes	121	.Polarization
73	<b>RECIRCULATION STORES</b>	122	..Magneto-optical
74	.Magnetic	123	.Bragg cells
75	.Stepwise	124	.Diffraction
76	.Delay lines	125	..Holograms
77	.Plural paths	126	.Thermoplastic
78	<b>PLURAL SHIFT REGISTER MEMORY DEVICES</b>	127	.Transparency
80	<b>MAGNETIC SHIFT REGISTERS</b>	128	.Electron beams
81	.Bidirectional	129	<b>SYSTEMS USING PARTICULAR ELEMENT</b>
82	.Two cells per bit	130	.Three-dimensional magnetic array
83	.SiPo/PiSo	131	.Two magnetic cells per bit
84	.Core in transfer loop	132	.Different size cores
85	.Continuous	133	.Cells of diverse coercivity
86	..Plated wire	134	.Continuous cells
87	.Thin film	135	..Elongated or bar-shaped cell
88	..Domain tip	136	...Twisters
89	.Logic	137	...Tubular
90	.Multiaperture cell	138	...Chain
91	..Ladder	139	...Plated wire
92	..With other type core	140	.Multiaperture cell
93	.Including delay means	141	..Aperture plate
94	<b>READ ONLY SYSTEMS (I.E.. SEMIPERMANENT)</b>	142	..Aperture with transverse axis
95	.With override (i.e., latent images)	143	...Biax
96	.Fusible	144	..Same size apertures
97	.Magnetic	145	.Ferroelectric
98	..Random core	146	.Electrets
99	..Random wiring	147	.Persistent internal polarization (PIP)
100	.Resistive	148	.Resistive
101	.Inductive	149	.Capacitors
102	.Capacitative	150	..Inherent
103	.Semiconductive	151	.Molecular or atomic
104	..Transistors	152	..Nuclear induction or spin echo
105	..Diodes	153	.Electrochemical
106	<b>RADIANT ENERGY</b>	154	.Flip-flop (electrical)
107	.Chemical fluids	155	..Plural emitter or collector
108	.Liquid crystal	156	..Complementary
109	.Photoconductive and ferroelectric	157	.Magnetostrictive or piezoelectric
110	.Electroluminescent and photoconductive	158	.Magnetoresistive
		159	.Negative resistance
		160	.Superconductive
		161	..Thin film

162	..Josephson	200	.Bad bit
163	.Amorphous (electrical)	201	.Testing
164	.Electrical contacts	202	.Complementing/balancing
165	..Coherer	203	.Precharge
166	..Relay	204	.Accelerating charge or discharge
167	.Simulating biological cells	205	.Flip-flop used for sensing
168	.Ternary	206	.Noise suppression
169	.Gunn effect	207	..Differential sensing
170	.Hall effect	208	...Semiconductors
171	.Magnetic thin film	209	...Magnetic
172	..Isotropic	210	....Reference or dummy element
173	..Multiple magnetic storage layers	211	..Temperature compensation
174	.Semiconductive	212	...Semiconductor
175	..Diodes	213	...Magnetic
176	..Silicon on sapphire (SOS)	214	..Particular wiring
177	..Bioplar and FET	215	.Optical
178	..Ion implantation	216	..Holographic
179	..Plural emitter or collector	217	.Electron beam
180	..Four layer devices	218	.Erase
181	..Complementary conductivity	219	.SiPo/PiSo
182	..Insulated gate devices	220	.Parallel read/write
183	...Charge coupled	221	.Serial read/write
184	...Variable threshold	222	.Data refresh
186	..Single device per bit	223	.Bridge
187	..Three devices per bit	224	.Eddy current
188	..Four or more devices per bit	225	.Minor loop
189.01	<b>READ/WRITE CIRCUIT</b>	225.5	.Including magnetic element
189.02	.Multiplexing	225.6	.Having bipolar circuit element
189.03	.Plural use of terminal	225.7	.Having fuse element
189.04	.Simultaneous operations (e.g., read/write)	226	<b>POWERING</b>
189.05	.Having particular data buffer or latch	227	.Conservation of power
189.06	.Including signal clamping	228	.Data preservation
189.07	.Including signal comparison	229	..Standby power
189.08	.Including specified plural element logic arrangement	230.01	<b>ADDRESSING</b>
189.09	.Including reference or bias voltage generator	230.02	.Multiplexing
189.11	.Including level shift or pull-up circuit	230.03	.Plural blocks or banks
189.12	.With shift register	230.04	..Alternate addressing (e.g., even/odd)
190	.For complementary information	230.05	.Multiple port access
191	.Signals	230.06	.Particular decoder or driver circuit
192	..Radio frequency	230.07	..Including magnetic element
193	..Strobe	230.08	.Including particular address buffer or latch circuit arrangement
194	..Delay	230.09	.Combined random and sequential addressing
195	..Inhibit	231	.Using selective matrix
196	...Sense/inhibit	232	..Magnetic
197	..Microwave	233	.Sync/clocking
198	..Transmission	233.5	..Transition detection
199	..Coincident A.C. signal with pulse	234	.Optical
		235	..Page memories
		236	.Counting

237 .Electron beam  
238 .Cartesian memories  
238.5 .Byte or page addressing  
239 .Sequential  
240 ..Using shift register  
241 ..Detectors  
242 .Current steering  
243 ..Diode  
243.5 .Including magnetic element  
244 **MISCELLANEOUS**

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